

# **VDIC EEPROM MEMORY**

## **VDEE8M32XS64XX8V250-II USER MANUAL**

**Version : A0**

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# VDIC-EEPROM

## 3.3V 256K× 32bit

### 1 Description

The VDEE8M32XS64XX8V250-II is a 256K× 32bit Electrically Erasable and Programmable CMOS ROM. It is organized as two banks of 4Mbit(128k×32). Each bank has 32-bit interface and is selected with specific #CEn. All other signals are common to the eight EEPROM 1Mbit. The device is manufactured using well known SIP technology. It is particularly well suited for use in high reliability, high performance and high density system applications.

The VDEE8M32XS64XX8V250-II is packaged in a 64 pins SOP

### 2 Features

- Single 3.3 V supply: 2.7 V to 3.6 V
- Access time: 250 ns (max)
- Power dissipation
  - Active: 80 mW/MHz, (typ)
  - Standby: 880 μW (max)
- On-chip latches: address, data, #CE, #OE, #WE
- Automatic byte write: 10 ms (max)
- Automatic page write (128 bytes): 10 ms (max)
- Data polling and RDY/#Busy
- Data protection circuit on power on/off
- Conforms to JEDEC byte-wide standard
- Reliable CMOS with MNOS cell technology
- 10<sup>4</sup>erase/write cycles (in page mode)
- 10 years data retention
- Software data protection
- Write protection by #RES pin

### 3 Block Diagram

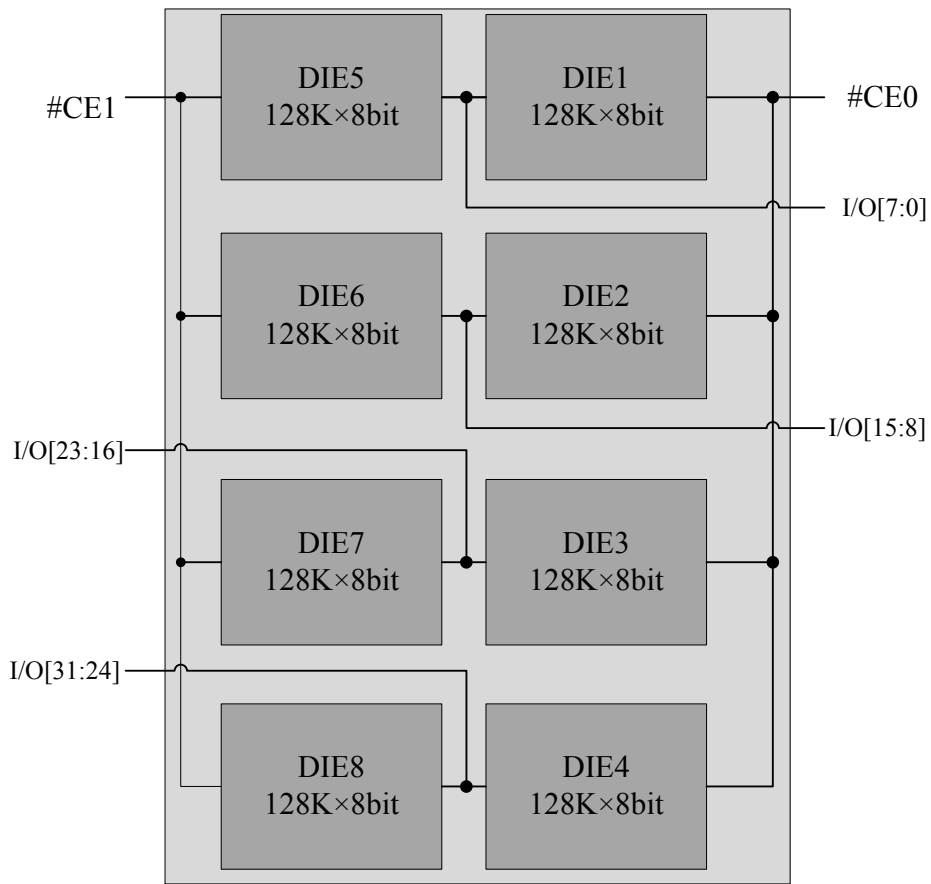


Figure 1 Block diagram

### 4 Pin Descriptions

Pin Id	Pin #	Pin Id
A11	1	64
A9	2	63
A8	3	62
A4	4	61
A5	5	60
A6	6	59
A7	7	58
A12	8	57
A14	9	56
A16	10	55
RDY/#BUSY	11	54
VCC	12	53
VCC	13	52
VCC	14	51
VCC	15	50
A15	16	49
#RES	17	48
#WE	18	47
A13	19	46
A0	20	45
A1	21	44
A2	22	43
A3	23	42
VSS	24	41
VSS	25	40
VSS	26	39
VSS	27	38
#CE0	28	37
NC	29	36
#CE1	30	35
A10	31	34
#OE	32	33

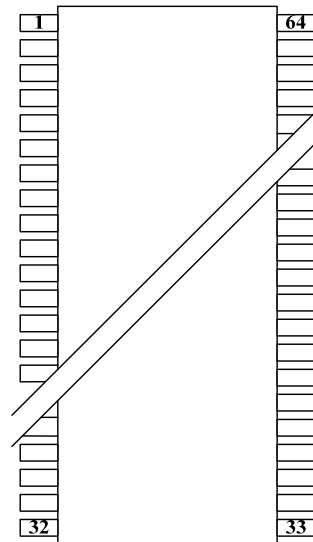


Figure 2 Pin configuration

Table 1 Pin description

Name	Function
A0~A16	Address Input..
I/O0- I/O31	Data Input/Output Ports. 32 bit-directional ports are used to read data from or write data into the EEPROM.
#CE0	Die Enable Input .When #CEn is Low, the command input cycle becomes valid. When #CEn is High, all inputs are ignored.
#CE1	
RDY/#BUSY	Ready busy.
#RES	Reset
#OE	Output enable.
#WE	Write Enable Input. Enables write operation.
VCC	Power supply
VSS	Ground

## 5 Command Operation

### 5.1 Absolute Maximum Ratings

Table 2 Absolute maximum ratings

Parameter	Symbol	Value	Unit
Supply voltage relative to V <sub>SS</sub>	V <sub>CC</sub>	-0.6 to +7.0	V
Input voltage relative to V <sub>SS</sub>	V <sub>IN</sub>	-0.5 to +7.0	V
Operating temperature range	T <sub>OPR</sub>	-55 to +125	°C
Storage temperature range	T <sub>STG</sub>	-65 to +150	°C
Power Dissipation	P <sub>D</sub>	1.0	W

### 5.2 Recommended DC Operating Conditions

Table 3 Recommended DC operating condition

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V <sub>CC</sub>	2.7	3.3	3.6	V
	V <sub>SS</sub>	0	0	0	V
Input voltage	V <sub>IL</sub>	-0.3	-	0.8	V
	V <sub>IH</sub>	1.9	-	V <sub>CC</sub> +0.3	V
	V <sub>H</sub>	V <sub>CC</sub> -0.5	-	V <sub>CC</sub> +1.0	V

### 5.3 DC Characteristics (V<sub>CC</sub> = 2.7 V to 3.6 V)

Table 4 DC characteristics

Parameter	Symbol	Test conditions	min.	max.	Unit
Output voltage low level	V <sub>OL</sub>	V <sub>CC</sub> =2.7V , I <sub>OL</sub> = 2.1mA	—	0.4	V
Output voltage high level	V <sub>OH</sub>	V <sub>CC</sub> =2.7V , I <sub>OH</sub> = -400uA	2.16	—	V

## 6 Typical Application

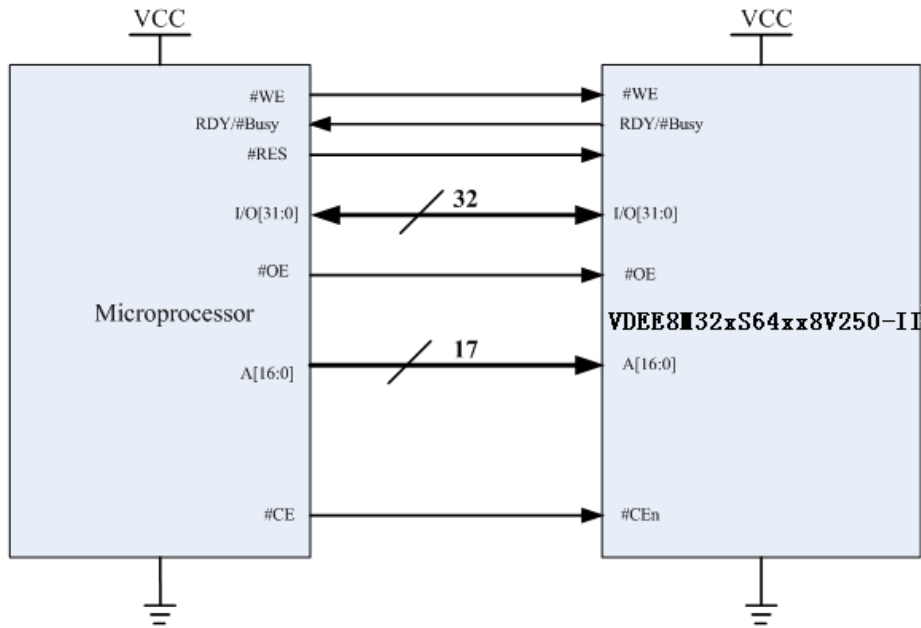


Figure 3 Typical application

## 7 Ordering Information

<b>1</b>	<b>2</b>	<b>3</b>	<b>4</b>	<b>5</b>	<b>6</b>	<b>7</b>	<b>8</b>	<b>9</b>	<b>10</b>	<b>11</b>	<b>12</b>	<b>13</b>
<u>VD</u>	<u>EE</u>	<u>8M</u>	<u>32</u>	<u>X</u>	<u>S</u>	<u>64</u>	<u>X</u>	<u>X</u>	<u>8</u>	<u>V</u>	<u>250</u>	<u>II</u>
VDIC												
EEPROM												
Capability: 8M bit												
Bus Width: 32bit												
R= Radiation Data Tested; V= Generic Radiation Data Available												
Package: SOP												
Pin Quantity: 64 Pin												
Temperature: E=0~+70°C;I=-40~+85°C;M=-55~+125°C												
Quality: E= Sample; B= Industry; M=Military; S= Space												
Stacking Layer: 8 layer												
Typical Operating Voltage : 3.3V												
Speed: 250ns												
II=Second Version												

Table 5 Ordering information

Part Number	Capacity (bit)	Bus Width (bit)	Radiation			Packaging	Temperature ( °C )
			TID <sup>1</sup>	SEL <sup>2</sup>	SEU <sup>3</sup>		
VDEE8M32VS64EE8V250-II	8M	32	-	-	-	SOP64	0 ~+70
VDEE8M32VS64IB8V250-II	8M	32	-	-	-	SOP64	-40 ~+85
VDEE8M32VS64MM8V250-II	8M	32	-	-	-	SOP64	-55 ~+125
VDEE8M32RS64MS8V250-II	8M	32	TBD	TBD	TBD	SOP64	-55 ~+125

<sup>1</sup> TID: Total Dose (Krad(Si))

<sup>2</sup> SEL: LET Threshold (Mev.cm<sup>2</sup>/mg)

<sup>3</sup> SEU:SEU Threshold (Mev.cm<sup>2</sup>/mg)



### 8 Package Dimensions

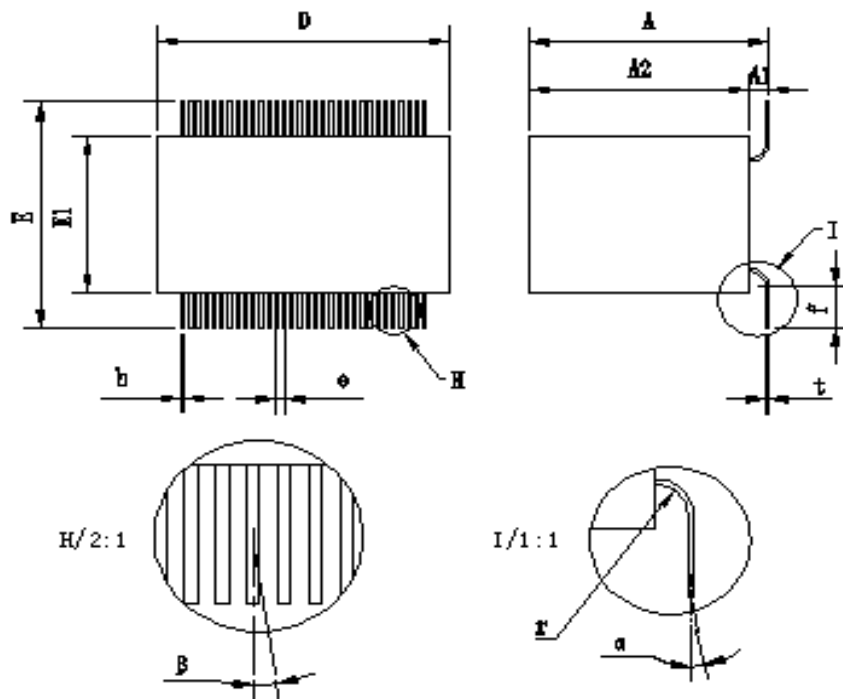


Figure 4 Package dimensions

Table 6 Dimensions information

	Min	Max
A	14.90	15.80
A2	13.70	14.50
D	18.50	18.90
E	15.80	16.20
E1	10.80	11.20
f	2.9	
b	0.25	
e	0.5	
r	1.0	
t	0.2	
$\alpha$	$\leq 3^\circ$	
$\beta$	$\leq 3^\circ$	
NOTE: 1.Uint: mm 2. A1=A - A2		

## 9 REVISION HISTORY

Table 7 Revision history

Revision	Date	Description of Change
A0	Sep 09,2019	First Created